

N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ZVN4306A

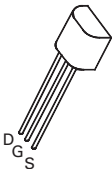
ISSUE 3 – JULY 94

FEATURES

- * 60 Volt V_{DS}
- * $R_{DS(on)} = 0.33\Omega$
- * Spice model available

APPLICATIONS

- * DC-DC convertors
- * Solenoids / relay drivers for automotive



**E-Line
TO92 Compatible**

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	1.1	A
Practical Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_{DP}	1.3	A
Pulsed Drain Current	I_{DM}	15	A
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	850	mW
Practical Power Dissipation at $T_{amb}=25^{\circ}C$ *	P_{totp}	1.13	W
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}C$

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	60			V	$I_D=1mA, V_{GS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	1.3		3	V	$ID=1mA, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}			100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Zero Gate Voltage Drain Current	I_{DSS}			10 100	μA μA	$V_{DS}=60V, V_{GS}=0$ $V_{DS}=48V, V_{GS}=0V, T=125^{\circ}C(2)$
On-State Drain Current(1)	$I_{D(on)}$	12			A	$V_{DS}=10V, V_{GS}=10V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		0.22 0.32	0.33 0.45	Ω Ω	$V_{GS}=10V, I_D=3A$ $V_{GS}=5V, I_D=1.5A$
Forward Transconductance (1)(2)	g_{fs}	700			mS	$V_{DS}=25V, I_D=3A$

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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Input Capacitance (2)	C_{iss}			350	pF	$V_{DS}=25\text{ V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$
Common Source Output Capacitance (2)	C_{oss}			140	pF	
Reverse Transfer Capacitance (2)	C_{rss}			30	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$			8	ns	$V_{DD}=25\text{V}$, $V_{GEN}=10\text{V}$, $I_D=3\text{A}$
Rise Time (2)(3)	t_r			25	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$			30	ns	
Fall Time (2)(3)	t_f			16	ns	

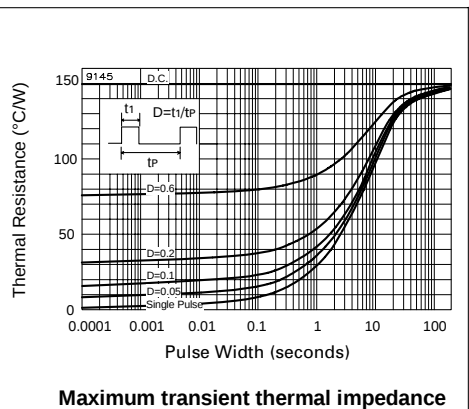
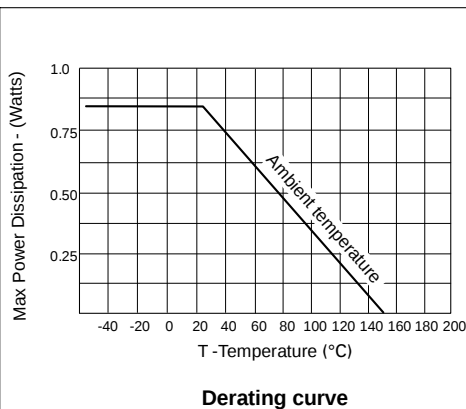
(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$

(2) Sample test.

(3) Switching times measured with 50 Ω source impedance and <5ns rise time on a pulse generator

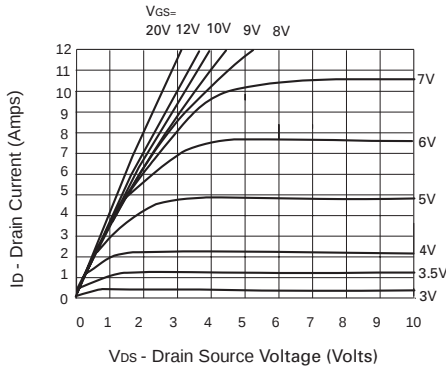
THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient	$R_{th(j-amb)}$	150	$^{\circ}\text{C/W}$
Junction to Case	$R_{th(j-case)}$	50	$^{\circ}\text{C/W}$

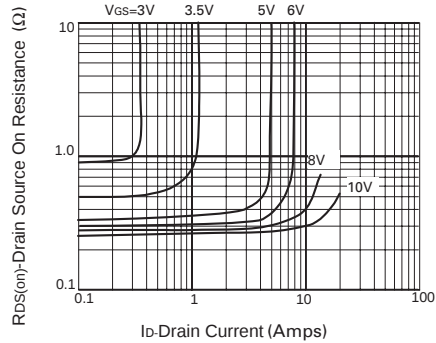


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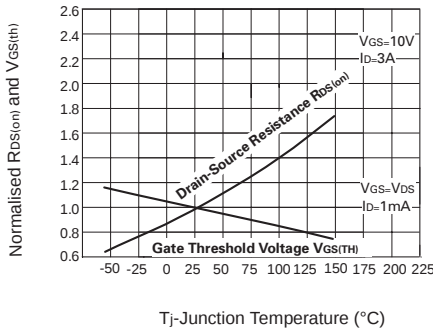
TYPICAL CHARACTERISTICS



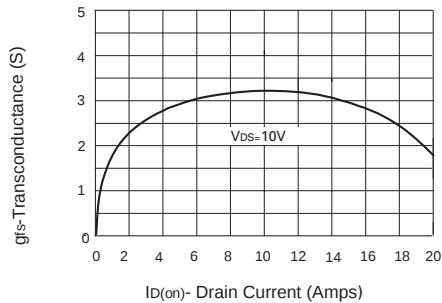
Saturation Characteristics



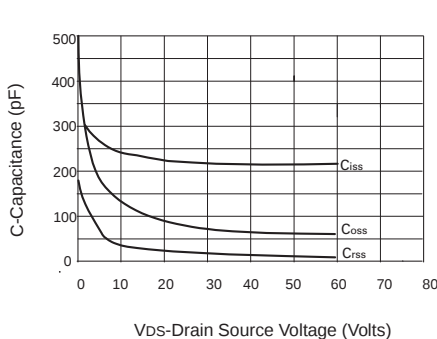
On-resistance v drain current



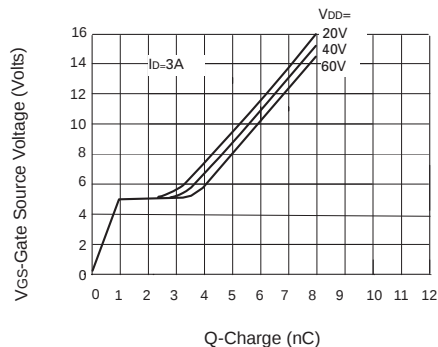
Normalised $R_{DS(on)}$ and $V_{GS(th)}$ v Temperature



Transconductance v drain current



Capacitance v drain-source voltage



Gate charge v gate-source voltage